U.S. Department of Commerce, Patent and Trademark Office	Atty Docket No.	Serial No.
	M-10937-1C	Continuation of Serial No. 09/263,654
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Applicant(s)	
(Use several sheets if necessary)	Wang, Shih-Yuan; Chen, Yong	
	Filing Date	Group
	Parent Application Filing Date: 3/5/99	2881

U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	6,153,010	11/28/00	Kiyoku et al.	117	95	
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

Foreign Patent Documents

							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
	AL	0 627 799 A1	12/07/94	EP	H01S	3/19		
	AM	0 851 542 A2	7/01/98	EP	H01S	3/00		
	AN	60235485	11/22/86	Japan Abstract only	H01S	3/18		
	AO	62212187	9/19/87	Japan Abstract only	H01S	3/18		
	AP	04127521	4/28/92	Japan Abstract only	H01L	21/20		

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	AQ	Zheleva, Tsvetanka, et al. "Pendeo-Epitaxy - A New Approach for Lateral Growth of Gallium Nitride Structures", Procedings of the Symposium GaN and related Alloys, Boston, Nov. 30-Dec.
	AR	Nakamura, Shuji, "InGaN Multiquantum = Weel-Structure Laser Diodes with GaN-AlGaN Modulation-Doped Strained-Layer Superlattices", IEEE Journal of Selected Topics in Quantum Electronics, Vol. 4, No. 1, May/June 1998, pp. 483-489.
	AS	Nakamura, Shuji, "Violet InGaN/GaN-Based Laser Diodes Operable at 50 Degrees C with a Fundimental Tansverse Mode", Japan Journal Applied Physics. Vol. 38, 1999, pp. L226-229.

Examiner	Date Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.